

**IN THE CLAIMS:**

Please delete Claims 2, 15. Furthermore, please enter the following clean version of amend Claims 1, 3, 7, 14, 16, 17, 19, and 20:

*B1*  
1. A method of fabricating an electronic device formed on a semiconductor wafer, comprising the steps of:

forming a layer of a first material in a fixed position relative to the wafer, wherein the first material has a dielectric constant less than 3.6;

5 forming a photoresist layer in a fixed position relative to the layer of the first material;

forming at least one void through the layer of the first material in response to the photoresist layer, thereby forming a polymeric residue in response to the photoresist layer ;

10 subjecting the semiconductor wafer to a plasma which incorporates a gas which includes hydrogen so as to remove the photoresist layer; and

removing the polymeric residue, the step of removing the polymeric residue comprises subjecting the semiconductor wafer to a mixture of hydrogen, oxygen, and fluorine.

*B2*  
3. The method of claim 1 wherein the step of removing the polymeric residue comprises subjecting the semiconductor wafer to a wet etch chemistry.

*B3*  
7. The method of claim 1 wherein the step of removing the polymeric residue comprises subjecting the semiconductor wafer to a combination of dilute hydrofluoric acid and an organic acid.

*B4*

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14. The method of claim 1 wherein the step of removing the polymeric residue comprises subjecting the semiconductor wafer to a dry plasma.

*B5*

16. The method of claim 1:  
wherein the hydrogen in the mixture is provided from a hydrogen source selected from a group consisting of H<sub>2</sub>, NH<sub>3</sub>, N<sub>2</sub>H<sub>2</sub>, H<sub>2</sub>S, and CH<sub>4</sub>; and  
wherein the fluorine in the mixture is provided from a fluorine source selected  
5 from a group consisting of CF<sub>4</sub>, C<sub>2</sub>F<sub>6</sub>, CHF<sub>3</sub>, CH<sub>2</sub>F<sub>2</sub>, SF<sub>6</sub>, CH<sub>3</sub>F, and NF<sub>3</sub>.

17. The method of claim 1 wherein the mixture further comprises an inert gas.

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*B6*

19. The method of claim 1 wherein the step of removing the polymeric residue comprises subjecting the semiconductor wafer to a mixture of at least 50% hydrogen, and approximately 2-20% oxygen and approximately 2-6% fluorine.

20. The method of claim 1 wherein the step of removing the polymeric residue comprises subjecting the semiconductor wafer to a mixture of approximately 80% NH<sub>3</sub>, approximately 10-15% N<sub>2</sub>, approximately 2-7% O<sub>2</sub>, and approximately 2-6% CF<sub>4</sub>.

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